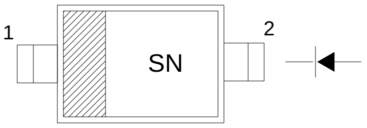
1N6263WT

SILICON SCHOTTKY BARRIER DIODE
for general purpose applications

The 1N6263WT is a metal on silicon schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "SN"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings ($T_a = 25^oC$)

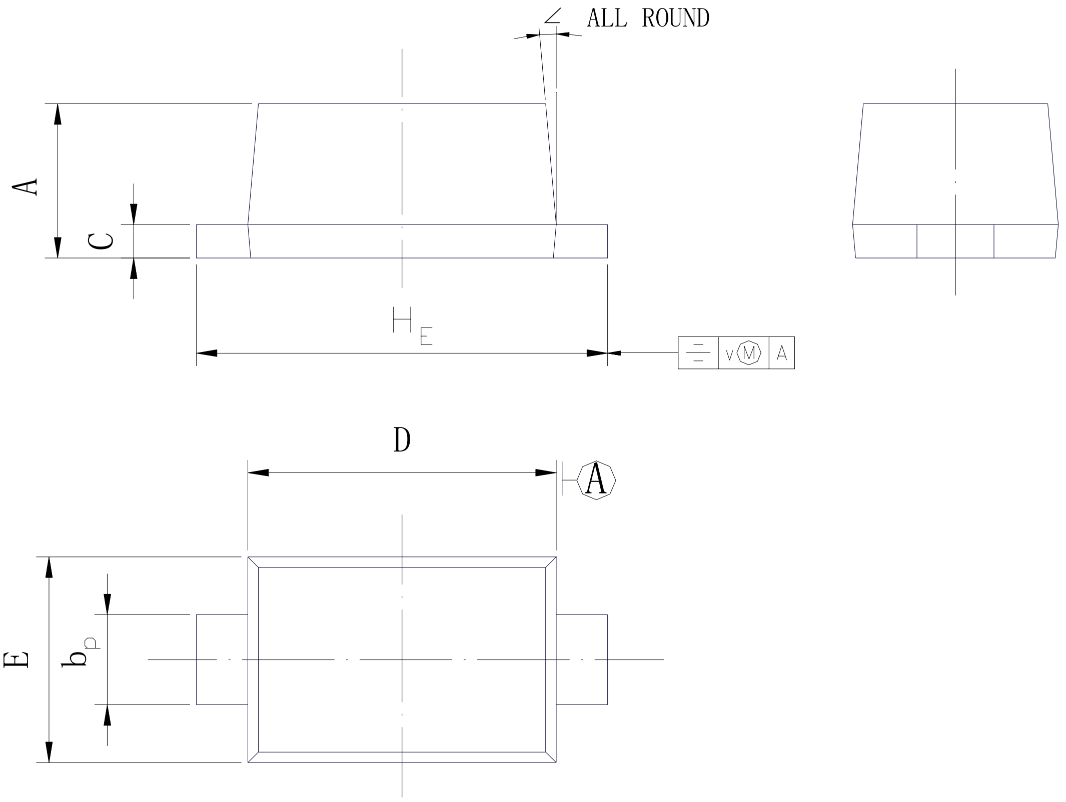
	Symbol	Value	Unit
Peak Reverse Voltage	V_{RRM}	40	V
Power Dissipation	P_{tot}	400[1)]	mW
Max. Single Cycle Surge 10 s Square wave	I_{FSM}	2	A
Junction Temperature	T_j	200	^OC
Storage Temperature Range	T_S	-55 to +200	^OC
[1)] Valid provided the leads direct at the case are kept at ambient temperature.			

Characteristics at $T_{amb} = 25^oC$

		Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10µA$		$V_{(BR)R}$	40	-	-	V
Forward Voltage Drop	at $I_F = 1mA$	V_F	-	-	0.39	V
	at $I_F = 15mA$	V_F	-	-	0.9	V
Leakage Current at $V_R = 30V$		I_R	-	-	200	nA
Junction Capacitance at $V_R = 0V$, f = 1MHz		C_{tot}	-	-	2.2	pF
Reverse Recovery Time at $I_F = I_R = 5mA$, recover to 0.1 I_R		t_{rr}	-	-	1	ns

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	v	∠
mm	0.70 0.60	0.4 0.3	0.135 0.127	1.25 1.15	0.85 0.75	1.65 1.55	0.1	5°